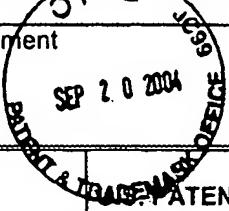


12/29/03

Form PTO-1449 (Modified)		Atty Docket No.: 42P18244		Serial No.: Unknown			
List of Patents and Publications Statement (Use several sheets if necessary)				Applicant: Justin K. Brask et al.			
				Filing Date : Herewith			
REFERENCE DESIGNATION			U.S. PATENT DOCUMENTS				
Examiner Initials		Document No.		Class	Sub-Class	Filing date if appropriate	
TL	AA	6,063,698	Tseng et al.	438	585		
	AB	6,184,072	Kaushik et al.	438	197		
	AC	6,420,279	Ono et al.	438	785		
	AD	6,475,874	Xiang et al.	438	396		
	AE	6,514,828	Ahn et al.	438	240		
	AF	6,544,906	Rotondaro et al.	438	785		
	AG	6,617,209	Chau et al.	438	240		
	AH	6,617,210	Chau et al.	438	240		
	AI	US2002/0197790	Kizilyalli et al.	438	240		
	AJ	US2003/032303	Yu et al.	438	770		
TL	AK	US2003/0045080	Visokay et al.	438	591		
FOREIGN PATENT DOCUMENTS							
	Document No.	Date	Country	Class	Sub-Class	Translation	
AL							
AM							
OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)							
TL	AN	Polishchuk et al. "Dual Workfunction CMOS Gate Technology Based on Metal Interdiffusion," www.eesc.berkeley.edu , 1 page					
	AO	Doug Barlage et al., "High-Frequency Response of 100nm Integrated CMOS Transistors with High-K Gate Dielectrics", 2001 IEEE, 4 pages.					
	AP	Lu et al., "Dual-Metal Gate Technology for Deep-Submicron CMOS Devices", dated April 29, 2003, 1 page.					
	AQ	Schwantes et al., "Performance Improvement of Metal Gate CMOS Technologies with Gigabit Feature Sizes", Technical University of Hanburg-Harburg, 5 pages.					
	AR	Doczy et al., "Integrating N-type and P-type Metal Gate Transistors", Serial No. 10/327,293, Filed December 20, 2002					
	AS	Brask et al., "A Method of Making Semiconductor Device Having a High-K Gate Dielectric", Serial No. 10/387,303, Filed March 11, 2003					
	AT	Brask et al., "A Method of Making Semiconductor Device Having a High-K Gate Dielectric", Serial No. 10/391,816, Filed March 18, 2003					
	AU	Chau et al., "A Method for Making a Semiconductor Device Having a Metal Gate Electrode", Serial No. 10/431,166, Filed May 6, 2003					
	AV	Brask et al. "A Selective Etch Process for Making a Semiconductor Device Having a High-K Gate Dielectric," Serial No. 10/652,546, filed August 28, 2003					
	AW	Brask et al. "A Method for Making a Semiconductor Device Having a High-K Gate Dielectric," Serial No. 10/642,796, filed August 28, 2003					
	AX	Brask, "Methods and Compositions for Selectively Etching Metal Films and Structures," Serial No. 10/658,225, filed September 8, 2003					
	AY	Brask et al., "A Method for Making a Semiconductor Device that Includes a Metal Gate Electrode", Serial No. Unknown, Filed December 18, 2003					
	AZ	Brask et al. "A Method for Making a Semiconductor Device with a Metal Gate Electrode that is Formed on an Annealed High-K Gate Dielectric Layer", Serial No. Unknown, Filed December 19, 2003					
	Examiner			Date Considered	02/28/05		

Form PTO-1449 (Modified)		Atty Docket No. R18244	Serial No.: 10/748,559				
List of Patents and Publications Statement (Use several sheets if necessary)			 Applicant: Justin K. Brask et al.				
			Filing Date: December 29, 2003				
REFERENCE DESIGNATION		PATENT DOCUMENTS					
Examiner Initials		Document No.		Class	Sub-Class		
TL	AA	6,410,376 B1	Ng et al.	438	199		
TL	AB	6,586,288 B2	Kim et al.	438	183		
TL	AC	US2002/0058374 A1	Kim et al.	438	228		
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FOREIGN PATENT DOCUMENTS							
		Document No.	Date	Country	Class	Sub-Class	Translation
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	AQ						
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	AX						
	AY						
	AZ						
Examiner		Date Considered	02/28/05				
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

Form PTO-1449 (Modified)

Atty Docket No.: P18244

Serial No.: 10/748,559

List of Patents and Publications Statement
(Use several sheets if necessary)O P E R A T I O N S
SEP 27 2004
P A T E N T
A D M I N I S T R A T I O N
Applicant: Justin K. Brask et al.

Filing Date: December 29, 2003

REFERENCE DESIGNATION

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D O C U M E N T S

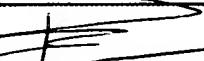
Examiner Initials		Document No.		Class	Sub-Class	Filing date if appropriate
TL	AA	6,255,698 B1	Gardner et al.	257	369	
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FOREIGN PATENT DOCUMENTS

		Document No.	Date	Country	Class	Sub-Class	Translation
TL	AP	EP 0 899 784 AZ	3/3/1999				
TL	AQ	GB 2 358 737 A	4/24/2001				
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OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)

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Examiner 

Date Considered

02/28/05

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Form PTO-1449 (Modified)		Atty Docket No.: P18244		Serial No.: 10/748,559			
List of Patents and Publications Statement (Use several sheets if necessary)				Applicant: Justin K. Brask et al.			
				Filing Date: December 29, 2003			
REFERENCE DESIGNATION		U.S. PATENT DOCUMENTS					
Examiner Initials		Document No.		Class	Sub-Class	Filing date if appropriate	
Z	AA	6,642,131 B2	Harada	438	591		
	AB	6,667,246 B2	Mitsuhashi et al.	438	756		
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Examiner		Date Considered					
		62/03/03 -					
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